

*CLAIM AMENDMENTS*

1. (Currently Amended) An interconnecting structure comprising:  
first wirings ~~formed~~ on a substrate;  
a low-k dielectric film ~~formed~~ on the first wirings, the low-k dielectric film having a dielectric constant ~~of not exceeding 3 or less~~;  
vias ~~formed~~ in the low-k dielectric film and connected to the first wiring;  
second wirings ~~formed~~ on the vias and connected to the vias; and  
dummy vias ~~formed~~ on the periphery of an isolated via of the vias.
2. (Currently Amended) The interconnecting structure according to claim 1, further comprising a cap film ~~formed~~ on the low-k dielectric film, wherein the second ~~wiring is~~ wirings are formed in the cap film and the low-k dielectric film.
3. (Currently Amended) The interconnecting structure according to claim 1, further comprising:  
first dummy wirings ~~formed~~ on the periphery of the first wirings; and  
second dummy wirings ~~formed~~ on the periphery of the second wirings, wherein the dummy vias ~~are is~~ connected to the first and second dummy wirings, and one of the first ~~or~~ and second dummy wirings connected to the dummy vias are connected to a ground potential.
4. (Original) The interconnecting structure according to claim 1, wherein the dummy vias have a slit shape.
5. (Currently Amended) The interconnecting structure according to claim 1, wherein ~~the dimension of the dummy vias is~~ have a dimension 1 to 10 times ~~the~~ a minimum dimension of the vias.